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(Use several sheets if necessary)

Applicant

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## U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
J.B.	1.	05/18/1999	5,904,597	Doi et al.			

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO
J.B.	2.	02/10/1994	JP 06-37355	Japan			Abstract
J.B.	3.	07/30/1994	GB 2309582 A	Great Britain			
J.B.	4.	10/13/1995	JP 07-263857	Japan			Abstract
J.B.	5.	03/14/1996	DE 19531132 A	Germany			Abstract
J.B.	6.	08/05/1997	JP 09-205254	Japan			Abstract
J.B.	7.	10/31/1997	JP 09-283857	Japan			Abstract

## OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
J.B.	8.	Nakahara, K. et al., (April, 1998) "1.3- $\mu$ m Continuous-Wave Lasing Operation in GaInNAs Quantum-Well Lasers," <i>Photonics Technology Letters</i> 10(4): 487-488.
J.B.	9.	Tanaka, S. et al. (1998) "Improvement of Optical Properties of GaNAs Epitaxial Films by Thermal Annealing," <i>Jpn. J. Appl. Phys.</i> 28p-ZM-12:290 (Abstract only).
J.B.	10.	Uesugi, K. and Suemune, I. (1997) "Bandgap Energy of GaNAs Alloys Grown on (001) GaAs by Metalorganic Molecular Beam Epitaxy," <i>Jpn. J. Appl. Phys.</i> 36(12A):L1572-L1573

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DATE CONSIDERED: Nov. 19, 2002

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